

Ting-Chang Chang

List of Publications by Year in descending order

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512
papers

9,808
citations

50170

46
h-index

79541

73
g-index

516
all docs

516
docs citations

516
times ranked

5446
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigating Selectorless Property within Niobium Devices for Storage Applications. ACS Applied Materials & Interfaces, 2022, 14, 2343-2350.	4.0	10
2	Increasing Controllable Oxygen Ions to Improve Device Performance Using Supercritical Fluid Technique in ZnO-Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2022, 69, 127-132.	1.6	1
3	Influences of aluminum doping on the microstructures and electrical properties of tantalum nitride thin films before and after annealing. Vacuum, 2022, 197, 110791.	1.6	4
4	Effects of X-ray accelerating voltage on electrical properties and reliability for ferroelectric random-access memory (FeRAM). Applied Physics Express, 2022, 15, 034002.	1.1	0
5	Improvement of Strained Negative Bias Temperature Instability in Flexible LTPS TFTs by a Stress-Release Design. IEEE Transactions on Electron Devices, 2022, 69, 1532-1537.	1.6	3
6	Analysis of self-heating-related instability in n-channel low-temperature polysilicon TFTs with different S/D contact hole densities. Applied Physics Express, 2022, 15, 034003.	1.1	1
7	Investigating two-stage degradation of threshold voltage induced by off-state stress in AlGaIn/GaN HEMTs. Semiconductor Science and Technology, 2022, 37, 025017.	1.0	1
8	Gate Dielectric Leakage Reduction in Hard-Mask Defined and Dry-Etch Patterned Organic TFTs Devices. IEEE Electron Device Letters, 2022, 43, 48-51.	2.2	2
9	Improving Drain-Induced Barrier Lowering Effect and Hot Carrier Reliability With Terminal via Structure on Half-Corbino Organic Thin-Film Transistors. IEEE Electron Device Letters, 2022, 43, 569-572.	2.2	1
10	Abnormal Two-Stage Degradation on P-Type Low-Temperature Polycrystalline-Silicon Thin-Film Transistor Under Hot Carrier Conditions. IEEE Electron Device Letters, 2022, 43, 721-724.	2.2	5
11	Abnormal On-Current Degradation Under Non-Conductive Stress in Contact Field Plate Lateral Double-Diffused Metal-Oxide-Semiconductor Transistor With 0.13- μ m Bipolar-CMOS-DMOS Technology. IEEE Electron Device Letters, 2022, 43, 769-772.	2.2	5
12	The Co-Improvement of Selectivity and Uniformity on NbO _x -Based Selector by Al-Doping. IEEE Electron Device Letters, 2022, 43, 870-873.	2.2	8
13	Enhancing Reliability and 2 mm-Axial Mechanical Bending Endurance by Gate Insulator Improvements in Flexible Polycrystalline Silicon TFTs. IEEE Transactions on Electron Devices, 2022, 69, 2423-2429.	1.6	2
14	Abnormal trend in hot carrier degradation with fin profile in short channel FinFET devices at 14 nm node. Semiconductor Science and Technology, 2022, 37, 045010.	1.0	1
15	Improved diffusion and storage of lithium ions via recrystallization induced conducting pathways in a LiTa ₂ O ₅ -based electrolyte for all-solid-state electrochromic devices with enhanced performance. Nanotechnology, 2022, 33, 275711.	1.3	2
16	Investigations on TaHf alloys for thin film resistor applications. Materials Chemistry and Physics, 2022, 285, 126027.	2.0	1
17	Suppressing Drain-Induced Barrier Lowering and Kink Effect in Low-Temperature Poly-Si TFTs Using a Partitioned Light Shield. IEEE Electron Device Letters, 2022, 43, 576-579.	2.2	0
18	A Functional Novel Logic for Max/Min Computing in One-Transistor-One-Resistor Devices With Resistive Random Access Memory (RRAM). IEEE Transactions on Electron Devices, 2022, 69, 1811-1815.	1.6	4

#	ARTICLE	IF	CITATIONS
19	A Method to Measure Polarization Signal of Nanoscale One-Transistor-One-Capacitor Ferroelectric Memory. IEEE Electron Device Letters, 2022, 43, 862-865.	2.2	0
20	Improving Reliability of a-InGaZnO TFTs With Optimal Location of Al ₂ O ₃ Passivation in Moist Environment. IEEE Transactions on Electron Devices, 2022, 69, 3181-3185.	1.6	3
21	Heterogeneous metal oxide channel structure for ultra-high sensitivity phototransistor with modulated operating conditions. Journal of Materials Chemistry C, 2022, 10, 9192-9197.	2.7	8
22	Physical Mechanism of the Mechanical Bending of High-Performance Organic TFTs and the Effect of Atmospheric Factors. ACS Applied Electronic Materials, 2022, 4, 3000-3009.	2.0	2
23	Investigation of the Self-Heating Effect in High Performance Organic TFTs With Multi-Finger Structure. IEEE Electron Device Letters, 2022, 43, 1243-1246.	2.2	2
24	Analysis of abnormal threshold voltage shift induced by surface donor state in GaN HEMT on SiC substrate. Applied Physics Letters, 2022, 120, 233505.	1.5	3
25	Advanced supercritical fluid technique to reduce amorphous silicon defects in heterojunction solar cells. Semiconductor Science and Technology, 2022, 37, 085011.	1.0	2
26	Analysis of Abnormal Current Rise Mechanism in GaN-MIS HEMT With Al ₂ O ₃ /Si ₃ N ₄ Gate Insulator Under Hot Switching. IEEE Transactions on Electron Devices, 2022, 69, 4218-4223.	1.6	1
27	Abnormal Hump and Two-Step Degradation of Top Gate a-InGaZnO TFTs Under Positive Bias Stress. IEEE Transactions on Electron Devices, 2022, 69, 4288-4292.	1.6	2
28	Abnormal Threshold Voltage Degradation Under Semi-On State Stress in Si ₃ N ₄ /AlGaIn/GaN-HEMT. IEEE Electron Device Letters, 2022, 43, 1420-1423.	2.2	5
29	Analysis of Meridian Flow Direction by Electrical Stimulation Method. Nanoscale Research Letters, 2022, 17, .	3.1	3
30	Comparison of physical electrical conductivity and acupuncture de-qi sensation between stainless steel needling and supercritical fluid-treated needling. Biomedical Journal, 2021, 44, S267-S274.	1.4	5
31	High-Density Memristor-CMOS Ternary Logic Family. IEEE Transactions on Circuits and Systems I: Regular Papers, 2021, 68, 264-274.	3.5	53
32	Cryptographic Key Generation and In Situ Encryption in One-Transistor-One-Resistor Memristors for Hardware Security. Advanced Electronic Materials, 2021, 7, 2001182.	2.6	11
33	Improvement of Hafnium Oxide Resistive Memory Performance Through Low-Temperature Supercritical Oxidation Treatments. IEEE Transactions on Electron Devices, 2021, 68, 541-544.	1.6	4
34	The time response for the low-temperature poly-silicon thin-film transistors to x-ray irradiation pulse. Semiconductor Science and Technology, 2021, 36, 045003.	1.0	1
35	Reliability enhancement in dipole-doped metal oxide semiconductor capacitor induced by low-temperature and high-pressure nitridation. Applied Physics Express, 2021, 14, 034002.	1.1	0
36	Degradation Behavior of Etch-Stopper-Layer Structured a-InGaZnO Thin-Film Transistors Under Hot-Carrier Stress and Illumination. IEEE Transactions on Electron Devices, 2021, 68, 556-559.	1.6	8

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37	The Relationship Between Resistive Protective Oxide (RPO) and Hot Carrier Stress (HCS) Degradation in n-Channel LD SOI MOSFET. IEEE Transactions on Electron Devices, 2021, 68, 962-967.	1.6	3
38	Realizing forming-free characteristic by doping Ag into HfO ₂ -based RRAM. Applied Physics Express, 2021, 14, 041008.	1.1	8
39	Analysis of Edge Effect Occurring in Non-Volatile Ferroelectric Transistors. IEEE Electron Device Letters, 2021, 42, 315-318.	2.2	7
40	Improving Performance by Inserting an Indium Oxide Layer as an Oxygen Ion Storage Layer in HfO ₂ -Based Resistive Random Access Memory. IEEE Transactions on Electron Devices, 2021, 68, 1037-1040.	1.6	10
41	On the Optimization of Performance and Reliability in a-InGaZnO Thin-Film Transistors by Versatile Light Shielding Design. IEEE Transactions on Electron Devices, 2021, 68, 1654-1658.	1.6	3
42	Analysis of increase in forward transconductance to determine the critical point of polarization at ferroelectric 1T1C memory. Applied Physics Letters, 2021, 118, .	1.5	2
43	Obtaining impact ionization-induced hole current by electrical measurements in gallium nitride metal-insulator-semiconductor high electron mobility transistors. Journal Physics D: Applied Physics, 2021, 54, 285104.	1.3	10
44	Comprehensive Regulation of the Threshold Oscillation for Neuromorphic Systems Based on Cryogenic Performance of NbO ₂ Device. IEEE Electron Device Letters, 2021, 42, 692-695.	2.2	8
45	Ultrahigh Uniformity and Stability in NbO ₂ -Based Selector for 3-D Memory by Using Ru Electrode. IEEE Transactions on Electron Devices, 2021, 68, 2255-2259.	1.6	9
46	Investigation of Degradation Behavior During Illuminated Negative Bias Temperature Stress in P-Channel Low-Temperature Polycrystalline Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2021, 42, 712-715.	2.2	3
47	Impact of AC Stress in Low Temperature Polycrystalline Silicon Thin Film Transistors Produced With Different Excimer Laser Annealing Energies. IEEE Electron Device Letters, 2021, 42, 847-850.	2.2	4
48	Gate Dielectric Breakdown in A-InGaZnO Thin Film Transistors With Cu Electrodes. IEEE Electron Device Letters, 2021, 42, 851-854.	2.2	7
49	Investigation of Thermal Behavior on High-Performance Organic TFTs Using Phase Separated Organic Semiconductors. IEEE Electron Device Letters, 2021, 42, 859-862.	2.2	9
50	An Analytical Method for Parameter Extraction in Oxide Semiconductor Field-Effect Transistors. IEEE Transactions on Electron Devices, 2021, 68, 2717-2722.	1.6	1
51	Enhancing gate turn-off thyristor blocking characteristics by low temperature defect passivation technology. Semiconductor Science and Technology, 2021, 36, 085005.	1.0	2
52	Abnormal hump in low temperature in SiGe devices with silicon capping insertion layer. Journal Physics D: Applied Physics, 2021, 54, 415105.	1.3	0
53	Charge Carrier Mobility and Series Resistance Extraction in 2D Field-Effect Transistors: Toward the Universal Technique. Advanced Functional Materials, 2021, 31, 2105003.	7.8	2
54	Improved uniformity and threshold voltage in NbO _x -ZrO ₂ selectors. Applied Physics Letters, 2021, 119, .	1.5	3

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55	Performance Improvement by Modifying Deposition Temperature in HfZrO _x Ferroelectric Memory. IEEE Transactions on Electron Devices, 2021, 68, 3838-3842.	1.6	7
56	Forming-free, ultra-high on-state current, and self-compliance selector based on titanium-doped NbOx thin films. Ceramics International, 2021, 47, 22677-22682.	2.3	12
57	Performance and Reliability Optimization of Supercritical-Nitridation-Treated AlGaIn/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2021, 68, 4317-4321.	1.6	1
58	Investigation of degradation behavior under negative bias temperature stress in Si/Si _{0.8} Ge _{0.2} metal-oxide-semiconductor capacitors. Journal Physics D: Applied Physics, 2021, 54, 475103.	1.3	1
59	Clarifying the switching layer transformation through analysis of an abnormal I _{on} -V curves with increasing set compliance current in oxide-based resistive random access memory. Applied Physics Express, 2021, 14, 094007.	1.1	0
60	Improving Breakdown Voltage in AlGaIn/GaN Metal-Insulator-Semiconductor HEMTs Through Electric-Field Dispersion Layer Material Selection. IEEE Transactions on Device and Materials Reliability, 2021, 21, 320-323.	1.5	6
61	Vertical Electric Field-Induced Abnormal Capacitance-Voltage Electrical Characteristics in a-InGaZnO TFTs. IEEE Transactions on Electron Devices, 2021, 68, 4431-4436.	1.6	0
62	Electrical Degradation of In Situ SiN/AlGaIn/GaN MIS-HEMTs Caused by Dehydrogenation and Trap Effect Under Hot Carrier Stress. IEEE Transactions on Electron Devices, 2021, 68, 4283-4288.	1.6	5
63	Comparison of the Hot Carrier Degradation of N- and P-Type Fin Field-Effect Transistors in 14-nm Technology Nodes. IEEE Electron Device Letters, 2021, 42, 1420-1423.	2.2	6
64	Performance enhancement of ZnGa ₂ O ₄ Schottky type deep-ultraviolet photodetectors by oxygen supercritical fluid treatment. Results in Physics, 2021, 29, 104764.	2.0	12
65	Dynamic Behaviors and Training Effects in TiN/Ti/HfO _x /TiN-Nanolayered Memristors with Controllable Quantized Conductance States: Implications for Quantum and Neuromorphic Computing Devices. ACS Applied Nano Materials, 2021, 4, 11296-11304.	2.4	2
66	Performance Enhancement of InGaZnO Top-Gate Thin Film Transistor With Low-Temperature High-Pressure Fluorine Treatment. IEEE Electron Device Letters, 2021, 42, 1611-1614.	2.2	3
67	Highly-Doped Region Optimization for Reduced Hot-Carrier Effects in Dual-Gate Low Temperature Polysilicon TFTs. IEEE Electron Device Letters, 2021, 42, 1794-1797.	2.2	2
68	Dynamic switching-induced back-carrier-injection in a-InGaZnO thin film transistors. Journal Physics D: Applied Physics, 2021, 54, 025111.	1.3	3
69	Investigation of the forming process under UV illumination in HfO ₂ -based resistance random access memory with a transparent electrode. Journal Physics D: Applied Physics, 2020, 53, 025104.	1.3	5
70	A characteristic improved technique and analysis with plasma treatment to the electrode on oxide-based resistive random access memory. Journal of Alloys and Compounds, 2020, 817, 150566.	2.8	2
71	Multi-Functional Controllable Memory Devices Applied for 3D Integration Based on a Single Niobium Oxide Layer. Advanced Electronic Materials, 2020, 6, 1900756.	2.6	12
72	Broadband Optoelectronic Synaptic Thin-Film Transistors Based on Oxide Semiconductors. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900630.	1.2	19

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73	Abnormal Increment Substrate Current After Hot Carrier Stress in n-FinFET. IEEE Electron Device Letters, 2020, 41, 15-18.	2.2	6
74	Inhibiting the Kink Effect and Hot-Carrier Stress Degradation Using Dual-Gate Low-Temperature Poly-Si TFTs. IEEE Electron Device Letters, 2020, 41, 54-57.	2.2	11
75	Investigating the Back-Channel Effect and Asymmetric Degradation Under Self-Heating Stress in Large Size a-InGaZnO TFTs. IEEE Electron Device Letters, 2020, 41, 58-61.	2.2	5
76	Abnormal threshold voltage shift caused by trapped holes under hot-carrier stress in a-IGZO TFTs. Journal Physics D: Applied Physics, 2020, 53, 085104.	1.3	3
77	Abnormal High Resistive State Current Mechanism Transformation in Ti/HfO ₂ /TiN Resistive Random Access Memory. IEEE Electron Device Letters, 2020, 41, 224-227.	2.2	11
78	Heterojunction Channels in Oxide Semiconductors for Visible-Blind Nonvolatile Optoelectronic Memories. Advanced Electronic Materials, 2020, 6, 2000747.	2.6	7
79	Adaptive Synaptic Memory via Lithium Ion Modulation in RRAM Devices. Small, 2020, 16, e2003964.	5.2	46
80	Improving a-InGaZnO TFTs Reliability by Optimizing Electrode Capping Structure Under Negative Bias Illumination Stress. IEEE Electron Device Letters, 2020, 41, 1221-1224.	2.2	5
81	Effect of ELA Energy Density on Self-Heating Stress in Low-Temperature Polycrystalline Silicon Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3163-3166.	1.6	9
82	Stabilizing resistive random access memory by constructing an oxygen reservoir with analyzed state distribution. Nanoscale, 2020, 12, 23532-23536.	2.8	5
83	In-Memory Hamming Weight Calculation in a 1T1R Memristive Array. Advanced Electronic Materials, 2020, 6, 2000457.	2.6	17
84	Effect of deposition temperature on electrical properties of one-transistor-one-capacitor (1T1C) FeRAM devices. Applied Physics Letters, 2020, 117, .	1.5	5
85	Enhancing LiAlO _x synaptic performance by reducing the Schottky barrier height for deep neural network applications. Nanoscale, 2020, 12, 22970-22977.	2.8	10
86	Enhancing Hot-Carrier Reliability of Dual-Gate Low-Temperature Polysilicon TFTs by Increasing Lightly Doped Drain Length. IEEE Electron Device Letters, 2020, 41, 1524-1527.	2.2	5
87	Realization of Synapse Behaviors Based on Memristor and Simulation Study With KMC Method. IEEE Journal of the Electron Devices Society, 2020, 8, 981-985.	1.2	2
88	Leakage Current in Fast Recovery Diode Suppressed by Low Temperature Supercritical Fluid Treatment Process. IEEE Electron Device Letters, 2020, 41, 1540-1543.	2.2	4
89	Enhancing Threshold Switching Characteristics and Stability of Vanadium Oxide-Based Selector With Vanadium Electrode. IEEE Transactions on Electron Devices, 2020, 67, 5059-5062.	1.6	7
90	Interface Defect Shielding of Electron Trapping in a-InGaZnO Thin Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3645-3649.	1.6	1

#	ARTICLE	IF	CITATIONS
91	A high-speed MIM resistive memory cell with an inherent vanadium selector. Applied Materials Today, 2020, 21, 100848.	2.3	11
92	Controllable Functional Layer and Temperature-Dependent Characteristic in Niobium Oxide Insulator-Metal Transition Selector. IEEE Transactions on Electron Devices, 2020, 67, 2771-2777.	1.6	13
93	Total-Dose Effect of X-ray Irradiation on Low-Temperature Polycrystalline Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2020, 41, 864-867.	2.2	7
94	Solution-processed amorphous Ga ₂ O ₃ :CdO TFT-type deep-UV photodetectors. Applied Physics Letters, 2020, 116, .	1.5	26
95	Effects of Redundant Electrode Width on Stability of a-InGaZnO Thin-Film Transistors Under Hot-Carrier Stress. IEEE Transactions on Electron Devices, 2020, 67, 2372-2375.	1.6	9
96	Abnormal Hump Effect Induced by Hydrogen Diffusion During Self-Heating Stress in Top-Gate Amorphous InGaZnO TFTs. IEEE Transactions on Electron Devices, 2020, 67, 2807-2811.	1.6	16
97	Investigation of HCD- and NBTI-Induced Ultralow Electric Field GIDL in 14-nm Technology Node FinFETs. IEEE Transactions on Electron Devices, 2020, 67, 2697-2701.	1.6	5
98	Abnormal hysteresis formation in hump region after positive gate bias stress in low-temperature poly-silicon thin film transistors. Journal Physics D: Applied Physics, 2020, 53, 405104.	1.3	4
99	A comprehensive study of enhanced characteristics with localized transition in interface-type vanadium-based devices. Materials Today Physics, 2020, 13, 100201.	2.9	8
100	A Novel Structure to Reduce Degradation Under Mechanical Bending in Foldable Low Temperature Polysilicon TFTs Fabricated on Polyimide. IEEE Electron Device Letters, 2020, 41, 725-728.	2.2	10
101	Origin of High Current and Illumination Stress Instability in Self-Aligned a-InGaZnO Thin Film Transistors With Al ₂ O ₃ as High- ϵ_r Gate Dielectric. IEEE Electron Device Letters, 2020, 41, 565-568.	2.2	11
102	Influence of Hot Carriers and Illumination Stress on a-InGaZnO TFTs With Asymmetrical Geometry. IEEE Electron Device Letters, 2020, 41, 745-748.	2.2	3
103	Hydrogen Diffusion and Threshold Voltage Shifts in Top-Gate Amorphous InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3123-3128.	1.6	25
104	In-Memory Digital Comparator Based on a Single Multivalued One-Transistor-One-Resistor Memristor. IEEE Transactions on Electron Devices, 2020, 67, 1293-1296.	1.6	16
105	Impact of Gate Size on Abnormal Current Rise Under an Electric Field in Organic Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 1143-1148.	1.6	1
106	Flexible low-temperature polycrystalline silicon thin-film transistors. Materials Today Advances, 2020, 5, 100040.	2.5	50
107	High-Precision Symmetric Weight Update of Memristor by Gate Voltage Ramping Method for Convolutional Neural Network Accelerator. IEEE Electron Device Letters, 2020, 41, 353-356.	2.2	31
108	Effects of X-ray Irradiation on the Noise Behavior of Amorphous Indium-Gallium-Zinc-Oxide TFTs. Journal of the Electrochemical Society, 2020, 167, 027512.	1.3	4

#	ARTICLE	IF	CITATIONS
109	One-Selector One-Resistor Devices: Multi-Functional Controllable Memory Devices Applied for 3D Integration Based on a Single Niobium Oxide Layer (Adv. Electron. Mater. 1/2020). Advanced Electronic Materials, 2020, 6, 2070002.	2.6	1
110	Improvement of Resistive Switching Characteristics in Zinc Oxide-Based Resistive Random Access Memory by Ammoniation Annealing. IEEE Electron Device Letters, 2020, 41, 357-360.	2.2	19
111	Strategies to Improve the Accuracy of Memristor-Based Convolutional Neural Networks. IEEE Transactions on Electron Devices, 2020, 67, 895-901.	1.6	49
112	Enhancement of Mechanical Bending Stress Endurance Using an Organic Trench Structure in Foldable Polycrystalline Silicon TFTs. IEEE Electron Device Letters, 2020, 41, 721-724.	2.2	8
113	Incorporation of Resistive Random Access Memory into Low-Temperature Polysilicon Transistor with Fin-Like Structure as 1T1R Device. Advanced Electronic Materials, 2020, 6, 2000066.	2.6	8
114	Low temperature defect passivation technology for semiconductor electronic devices"supercritical fluids treatment process. Materials Today Physics, 2020, 14, 100225.	2.9	16
115	Impact of electrode thermal conductivity on high resistance state level in HfO ₂ -based RRAM. Journal Physics D: Applied Physics, 2020, 53, 395101.	1.3	7
116	Investigation on the current conduction mechanism of HfZrO _x ferroelectric memory. Journal Physics D: Applied Physics, 2020, 53, 445110.	1.3	9
117	Advanced Low-Temperature"High-Pressure Hydrogen Treatment for Interface Defect Passivation in Si- and SiGe-Channel MOSCAPs. IEEE Transactions on Electron Devices, 2020, 67, 5403-5407.	1.6	12
118	Suppression of Edge Effect Induced by Positive Gate Bias Stress in Low-Temperature Polycrystalline Silicon TFTs With Channel Width Extension Over Source/Drain Regions. IEEE Transactions on Electron Devices, 2020, 67, 5552-5556.	1.6	8
119	Meridian study on the response current affected by electrical pulse and acupuncture. Nanoscale Research Letters, 2020, 15, 146.	3.1	6
120	Analyzing the interface trap density in SiGe capacitors using an abnormal flat band voltage shift at low temperature. Applied Physics Express, 2020, 13, 111006.	1.1	1
121	Corrections to "Total-Dose Effect of X-ray Irradiation on Low-Temperature Polycrystalline Silicon Thin-Film Transistors" [Jun 20 864-867]. IEEE Electron Device Letters, 2020, 41, 1448-1448.	2.2	0
122	An Ultra Energy-Saving Metal/Insulator/Metal Structure for One Selector-One RRAM. , 2020, , .		1
123	Design for Enhancing the Performance of Memristive Convolution Neural Network. , 2020, , .		0
124	An electro-photo-sensitive synaptic transistor for edge neuromorphic visual systems. Nanoscale, 2019, 11, 17590-17599.	2.8	71
125	Improving Reliability of High-Performance Ultraviolet Sensor in a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 1455-1458.	2.2	7
126	A Study of Effects of Metal Gate Composition on Performance in Advanced n-MOSFETs. IEEE Transactions on Electron Devices, 2019, 66, 3286-3289.	1.6	3

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127	Negative threshold voltage shift for LTPS TFTs under x-ray irradiation and gate bias. <i>Semiconductor Science and Technology</i> , 2019, 34, 095012.	1.0	3
128	Abnormal Unsaturated Output Characteristics In a-InGaZnO TFTs With Light Shielding Layer. <i>IEEE Electron Device Letters</i> , 2019, 40, 1281-1284.	2.2	2
129	Reliability Test Integrating Electrical and Mechanical Stress at High Temperature for a-InGaZnO Thin Film Transistors. <i>IEEE Transactions on Device and Materials Reliability</i> , 2019, 19, 433-436.	1.5	5
130	Indium Diffusion Behavior and Application in HfO ₂ -Based Conductive Bridge Random Access Memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1900285.	1.2	4
131	Realization of Storage and Synaptic Simulation Behaviors Based on Different Forming Modes. <i>IEEE Electron Device Letters</i> , 2019, 40, 1257-1260.	2.2	1
132	Hydrogen as a Cause of Abnormal Subchannel Formation Under Positive Bias Temperature Stress in a-InGaZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2954-2959.	1.6	12
133	Abnormal Positive Bias Temperature Instability Induced by Dipole Doped N-Type MOSCAP. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 897-901.	1.2	3
134	Functional Demonstration of a Memristive Arithmetic Logic Unit (MemALU) for In-Memory Computing. <i>Advanced Functional Materials</i> , 2019, 29, 1905660.	7.8	54
135	Analog Resistive Switching and Synaptic Functions in WO _x /TaO _x Bilayer through Redox-Induced Trap-Controlled Conduction. <i>ACS Applied Electronic Materials</i> , 2019, 1, 2422-2430.	2.0	41
136	The Effect of Humidity on Reducing Forming Voltage in Conductive-Bridge Random Access Memory With an Alloy Electrode. <i>IEEE Electron Device Letters</i> , 2019, 40, 1606-1609.	2.2	3
137	A Novel Heat Dissipation Structure for Inhibiting Hydrogen Diffusion in Top-Gate a-InGaZnO TFTs. <i>IEEE Electron Device Letters</i> , 2019, 40, 1447-1450.	2.2	17
138	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at $R = 2$ mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2019, 40, 913-916.	2.2	11
139	An Energy-Band Model for Dual-Gate-Voltage Sweeping in Hydrogenated Amorphous Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2614-2619.	1.6	4
140	Impact of Dehydrogenation Annealing Process Temperature on Reliability of Polycrystalline Silicon Thin Film Transistors. <i>IEEE Electron Device Letters</i> , 2019, 40, 1638-1641.	2.2	9
141	Overcoming Limited Resistance in 1T1R RRAM Caused by Pinch-Off Voltage During Reset Process. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 4706-4709.	1.6	8
142	Effect of a-InGaZnO TFT Channel Thickness under Self-Heating Stress. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q185-Q188.	0.9	2
143	Investigation of the Capacitance-Voltage Electrical Characteristics of Thin-Film Transistors Caused by Hydrogen Diffusion under Negative Bias Stress in a Moist Environment. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 40196-40203.	4.0	21
144	Analysis of Negative Bias Temperature Instability Degradation in p-Type Low-Temperature Polycrystalline Silicon Thin-Film Transistors of Different Grain Sizes. <i>IEEE Electron Device Letters</i> , 2019, 40, 1768-1771.	2.2	23

#	ARTICLE	IF	CITATIONS
145	Investigation of Mechanical Stress and Gate Bias Stress on Flexible Dual-Gate IGZO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2019, 50, 214-216.	0.1	0
146	A Dual-Gate InGaZnO ₄ -Based Thin-Film Transistor for High-Sensitivity UV Detection. Advanced Materials Technologies, 2019, 4, 1900106.	3.0	10
147	Optimal Tuning of Memristor Conductance Variation in Spiking Neural Networks for Online Unsupervised Learning. IEEE Transactions on Electron Devices, 2019, 66, 2844-2849.	1.6	14
148	Investigating Material Changes at Different Gadolinium Doping Power Levels in Indium-Tin Oxide Intended for Use as an Insulator in Resistive Switching Memory. IEEE Transactions on Electron Devices, 2019, 66, 2595-2599.	1.6	6
149	Enhancing Repetitive Uniaxial Mechanical Bending Endurance at R=2mm Using an Organic Trench Structure in Foldable Low Temperature Poly-Si Thin-Film Transistors. IEEE Electron Device Letters, 2019, , 1-1.	2.2	0
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